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Kind regards,

Team Nexperia



100 V, 1 A PNP low V_{CEsat} (BISS) transistor Rev. 02 — 22 November 2009

Product data sheet

Product profile 1.

1.1 General description

PNP low V_{CEsat} transistor in a SOT363 (SC-88) plastic package.

1.2 Features

- SOT363 package
- Low collector-emitter saturation voltage V_{CEsat}
- High collector current capability I_C and I_{CM}
- High efficiency leading to less heat generation

1.3 Applications

- Major application segments:
 - Automotive 42 V power
 - Telecom infrastructure
 - Industrial
- Peripheral driver:
 - Driver in low supply voltage applications (e.g. lamps and LEDs)
 - Inductive load driver (e.g. relays, buzzers and motors)
- DC-to-DC converter

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage		-	-	-100	V
I _C	collector current (DC)		-	-	-1	А
I _{CM}	peak collector current		-	-	-3	А
R _{CEsat}	equivalent on-resistance		-	-	320	mΩ



100 V, 1 A PNP low V_{CEsat} (BISS) transistor

2. Pinning information

Table 2.	Discrete pinning		
Pin	Description	Simplified outline	Symbol
1, 2, 5, 6	collector		
3	base		1, 2, 5, 6
4	emitter	0	3
			4 sym030

3. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
PBSS9110Y	-	plastic surface mounted package; 6 leads	SOT363		

4. Marking

	Marking	Table 4.
Marking code	nber	Type num
91* <mark>[1]</mark>	PBSS9110Y	
 91* <u>11</u>	0Y	

[1] * = p: made in Hong Kong* = t: made in Malaysia

* = W: made in China

100 V, 1 A PNP low V_{CEsat} (BISS) transistor

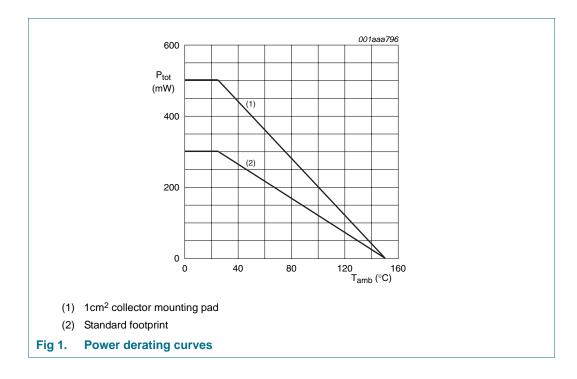
5. Limiting values

Table 5. In accorda	Limiting values nce with the Absolute Maximun	n Rating System (IE	EC 6	0134).		
Symbol	Parameter	Conditions		Min	Мах	Unit
V _{CBO}	collector-base voltage	open emitter		-	-120	V
V _{CEO}	collector-emitter voltage	open base		-	-100	V
V _{EBO}	emitter-base voltage	open collector		-	-5	V
I _{CM}	peak collector current	T _{j(max)}		-	-3	А
I _C	collector current (DC)			-	-1	А
I _B	base current (DC)			-	-0.3	А
P _{tot}	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$	[1]	-	290	mW
			[2]		480	mW
			[3]		625	mW
Tj	junction temperature			-	150	°C
T _{amb}	operating ambient temperature			-65	+150	°C
T _{stg}	storage temperature			-65	+150	°C

[1] Device mounted on a FR4 printed-circuit board, single-sided copper, tin-plated, standard footprint.

[2] Device mounted on a FR4 printed-circuit board, single-sided copper, tin-plated, 1cm² collector mounting pad.

[3] Device mounted on a FR4 printed-circuit board, single-sided copper, tin-plated, 6cm² collector mounting pad.



100 V, 1 A PNP low V_{CEsat} (BISS) transistor

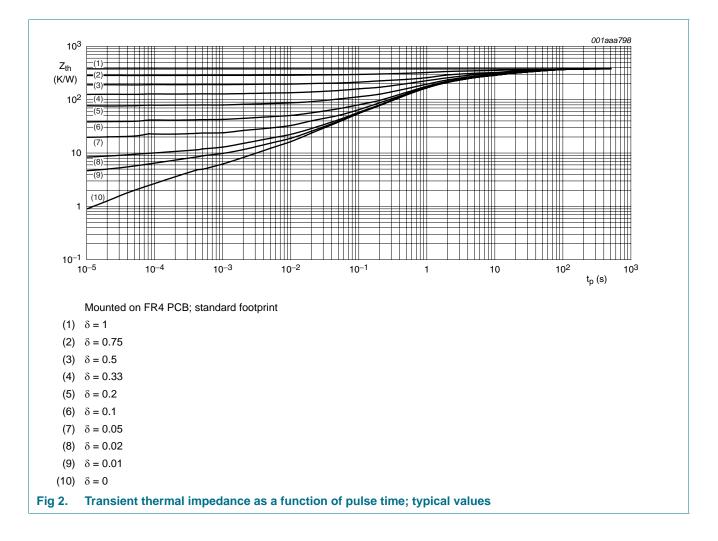
6. Thermal characteristics

Table 6.	Thermal characteristics				
Symbol	Parameter	Conditions		Тур	Unit
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	<u>[1]</u>	431	K/W
			[2]	260	K/W
			[3]	200	K/W
R _{th(j-s)}	thermal resistance from junction to soldering	in free air	<u>[1]</u>	85	K/W

[1] Device mounted on a FR4 printed-circuit board, single-sided copper, tin-plated, standard footprint

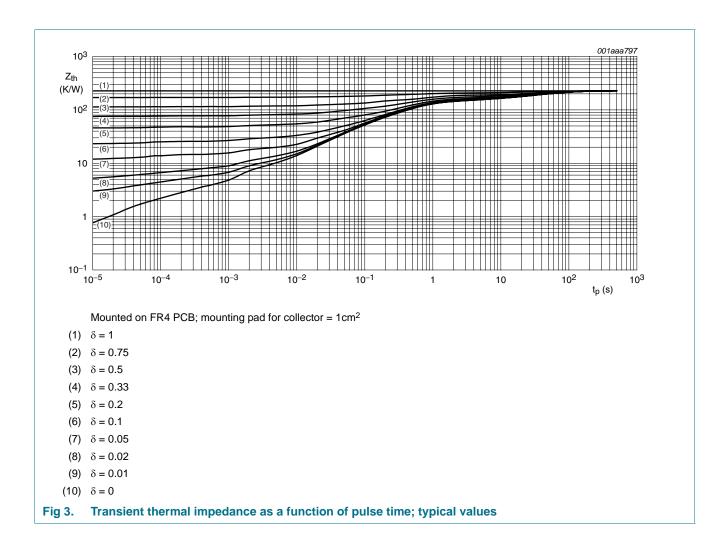
 $\label{eq:constraint} [2] \quad \text{Device mounted on a FR4 printed-circuit board, single-sided copper, tin-plated, 1cm^2 collector mounting pad.}$

[3] Device mounted on a FR4 printed-circuit board, single-sided copper, tin-plated, 6cm² collector mounting pad.



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100 V, 1 A PNP low V_{CEsat} (BISS) transistor



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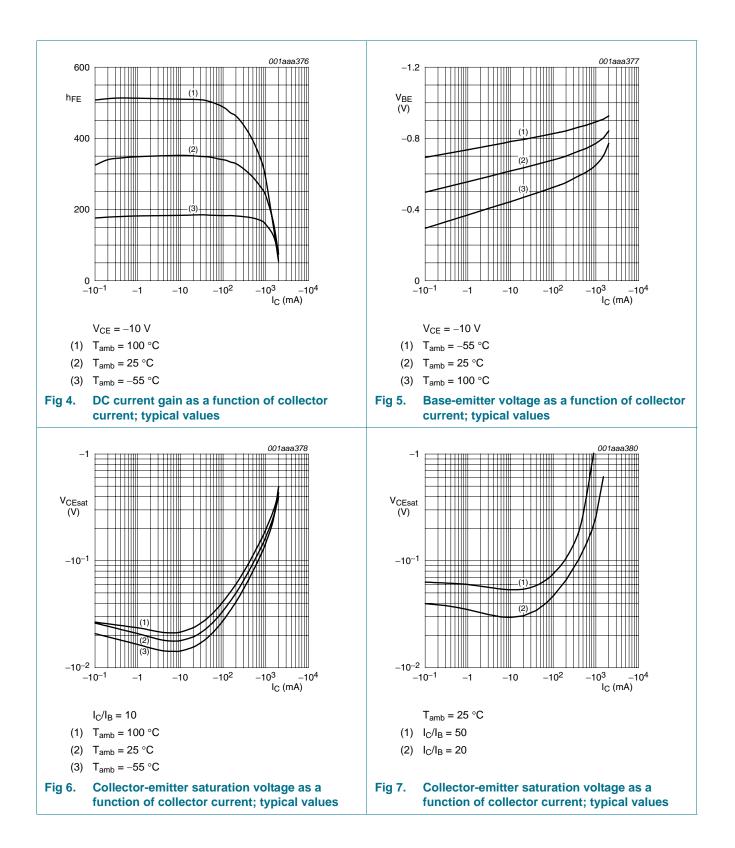
100 V, 1 A PNP low V_{CEsat} (BISS) transistor

7. Characteristics

	C unless otherwise spec						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off	$V_{CB} = -80 \text{ V}; I_E = 0 \text{ A}$		-	-	-100	nA
	current	$V_{CB} = -80 \text{ V}; I_E = 0 \text{ A};$ $T_j = 150 \text{ °C}$		-	-	-50	μΑ
I _{CES}	collector-emitter cut-off current	V_{CE} = -80 V; V_{BE} = 0 V		-	-	-100	nA
I _{EBO}	emitter-base cut-off current	$V_{EB} = -4 \text{ V}; \text{ I}_{C} = 0 \text{ A}$		-	-	-100	nA
h _{FE}	DC current gain	V_{CE} = -5 V; I_C = -1 mA		150	-	-	
		V_{CE} = -5 V; I_C = -250 mA		150	-	-	
		V_{CE} = –5 V; I_{C} = –0.5 A	<u>[1]</u>	150	-	450	
		$V_{CE} = -5 \text{ V}; \text{ I}_{C} = -1 \text{ A}$	<u>[1]</u>	125	-	-	
V _{CEsat}	collector-emitter saturation voltage	$I_C = -250 \text{ mA}; I_B = -25 \text{ mA}$		-	-	-120	mV
		$I_C = -500 \text{ mA}; I_B = -50 \text{ mA}$		-	-	-180	mV
		$I_{C} = -1 \text{ A}; I_{B} = -100 \text{ mA}$		-	-	-320	mV
R _{CEsat}	equivalent on-resistance	$I_{C} = -1$ A; $I_{B} = -100$ mA	<u>[1]</u>	-	170	320	mΩ
V _{BEsat}	base-emitter saturation voltage	$I_{C} = -1 \text{ A}; I_{B} = -100 \text{ mA}$		-	-	-1.1	V
V _{BEon}	base-emitter turn-on voltage	$I_{C} = -1 \text{ A}; V_{CE} = -5 \text{ V}$		-	-	-1.0	V
f⊤	transition frequency	$I_{C} = -50 \text{ mA}; V_{CE} = -10 \text{ V};$ f = 100 MHz		100	-	-	MHz
C _c	collector capacitance	$I_E = I_e = 0 \text{ A}; V_{CB} = -10 \text{ V};$ f = 1 MHz		-	-	17	pF

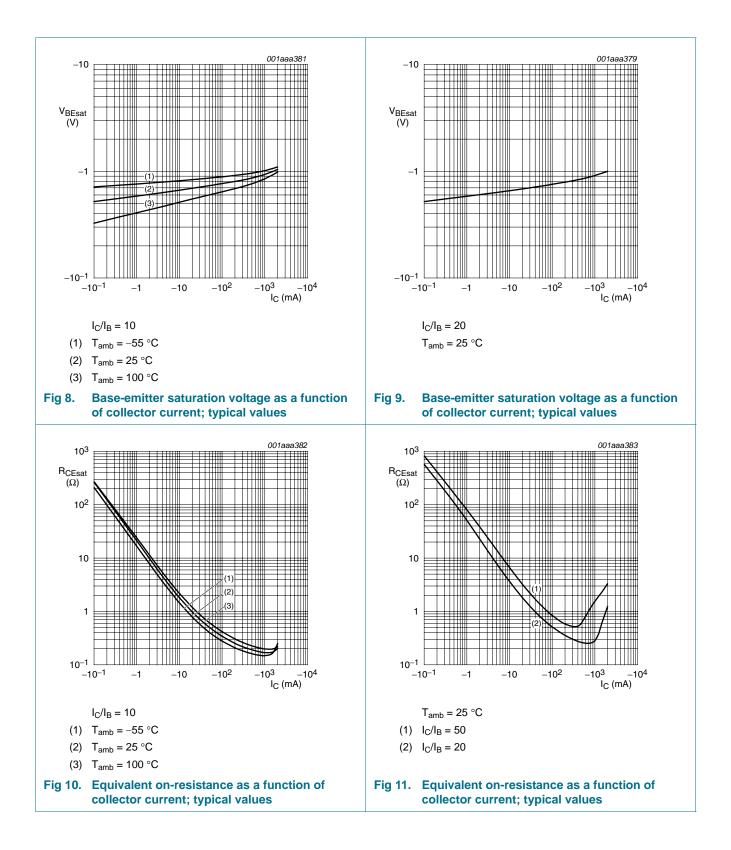
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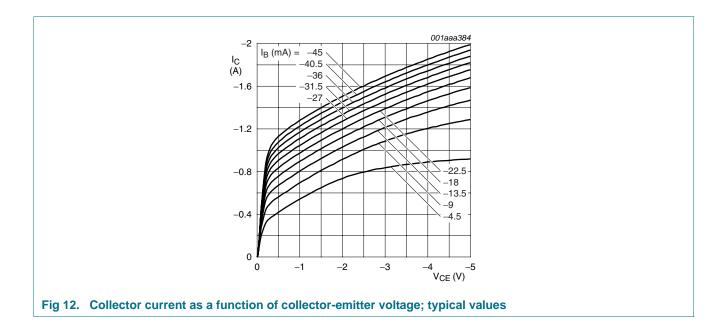
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100 V, 1 A PNP low V_{CEsat} (BISS) transistor



100 V, 1 A PNP low V_{CEsat} (BISS) transistor

8. Package outline

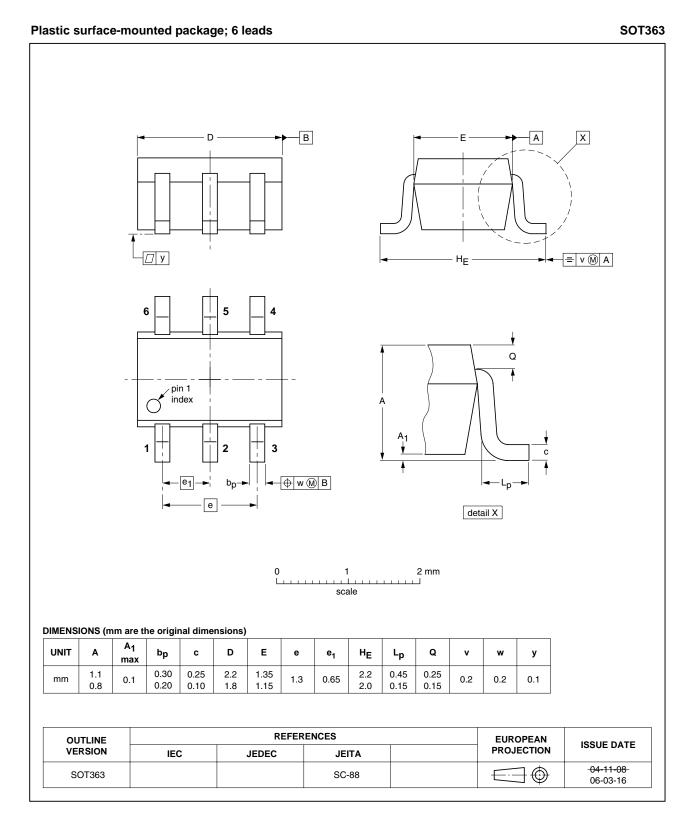


Fig 13. Package outline

PBSS9110Y_2

100 V, 1 A PNP low V_{CEsat} (BISS) transistor

9. Revision history

Table 8. Revision I	nistory					
Document ID	Release date	Data sheet status	Change notice	Supersedes		
PBSS9110Y_2	20091122	Product data	-	PBSS9110Y_1		
Modifications:	 This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content. 					
	<u>Table 2 "Discrete pinning"</u> : amended					
	• Figure 10 "Equivalent on-resistance as a function of collector current; typical values": updated					
	• Figure 11 "Equivalent on-resistance as a function of collector current; typical values": updated					
	• Figure 12 "Collector current as a function of collector-emitter voltage; typical values": updated					
	 Figure 13 "Page 	ckage outline": updated				
PBSS9110Y_1	20040609	Product data	-	-		

100 V, 1 A PNP low V_{CEsat} (BISS) transistor

10. Legal information

10.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

The term 'short data sheet' is explained in section "Definitions". [2]

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://w

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